

Is Now Part of



## **ON Semiconductor**®

# To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (\_), the underscore (\_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (\_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at <a href="mailto:www.onsemi.com">www.onsemi.com</a>. Please email any questions regarding the system integration to <a href="mailto:Fairchild\_questions@onsemi.com">Fairchild\_questions@onsemi.com</a>.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or unavteries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor and is officers, employees, uniotificated use, even if such claim any manner.

SEMICONDUCTOR

November 2013

## FQD7N20L N-Channel QFET<sup>®</sup> MOSFET 200 V, 5.5 A, 750 mΩ

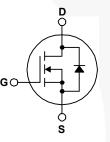
#### Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

#### Features

- 5.5 A, 200 V,  $R_{DS(on)}$  = 750 m $\Omega$  (Max.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 2.75 A
- Low Gate Charge (Typ. 6.8 nC)
- Low Crss (Typ. 8.5 pF)
- RoHS Compliant
- · Low Level Gate Drive Requirement Allowing Direct Operating from Logic Drivers





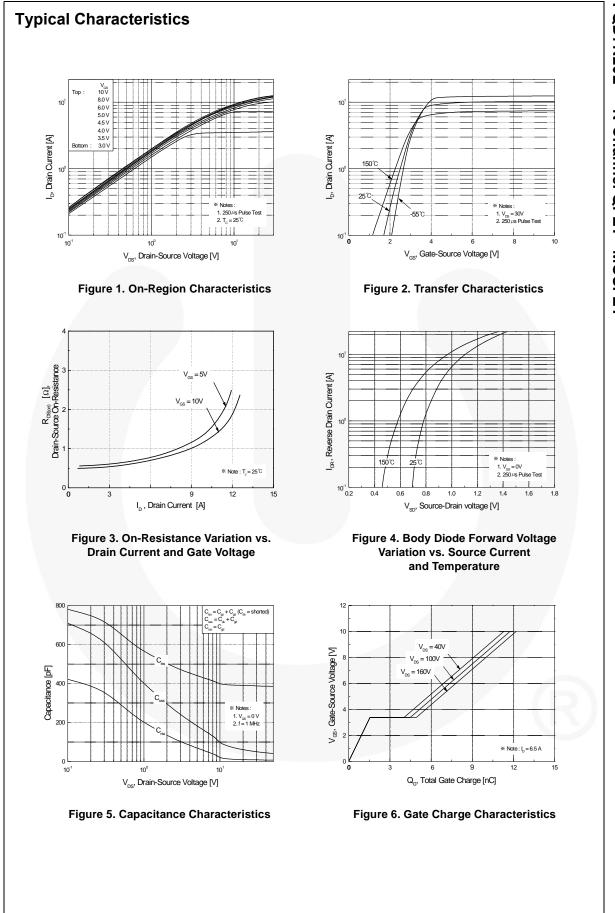
#### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

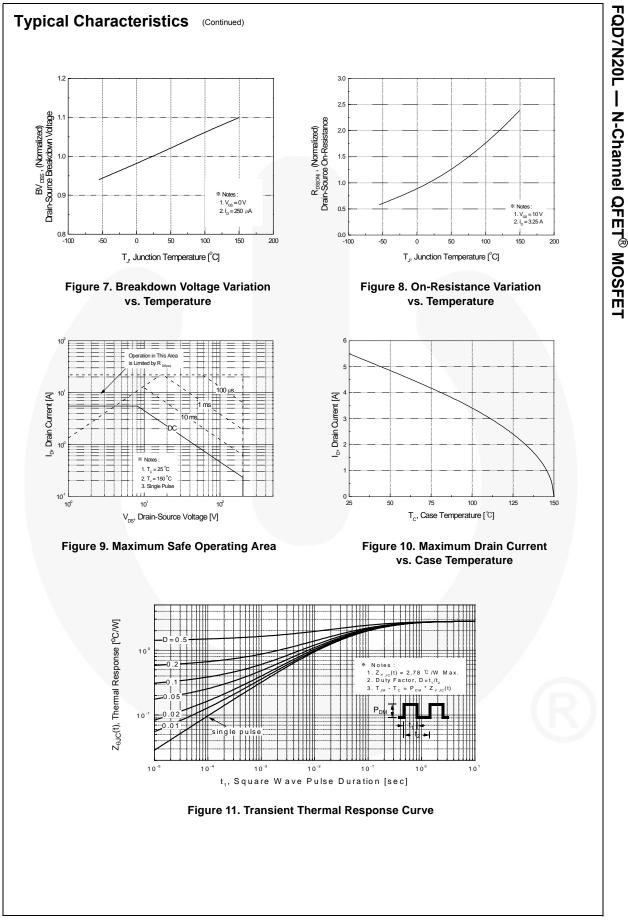
Symbol	Parameter	FQD7N20LTM	Unit
V <sub>DSS</sub>	Drain-Source Voltage	200	V
I <sub>D</sub>	Drain Current - Continuous ( $T_C = 25^{\circ}C$ )	5.5	А
	- Continuous (T <sub>C</sub> = 100°C)	3.48	A
I <sub>DM</sub>	Drain Current - Pulsed (Note 1)	22	A
V <sub>GSS</sub>	Gate-Source Voltage	± 20	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	73	mJ
I <sub>AR</sub>	Avalanche Current (Note 1)	5.5	A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	4.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>A</sub> = 25°C) *	2.5	W
	Power Dissipation (T <sub>C</sub> = 25°C)	45	W
	- Derate above 25°C	0.36	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C
TL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds	300	°C

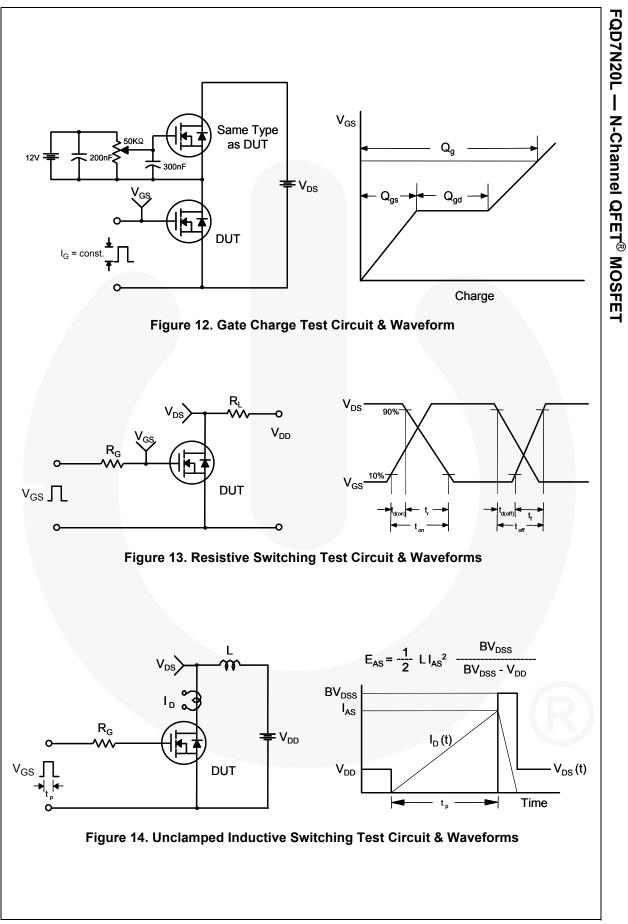
#### **Thermal Characteristics**

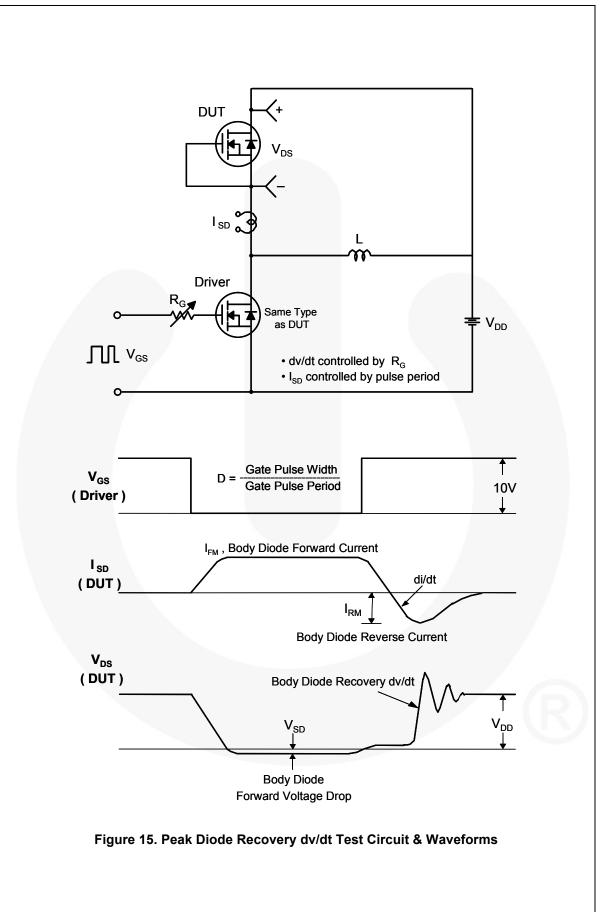
Symbol	Parameter	FQD7N20LTM	Unit	
$R_{\thetaJC}$	Thermal Resistance, Junction to Case, Max.	2.78		
Р	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W	
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient (*1 in <sup>2</sup> Pad of 2-oz Copper), Max.	50		

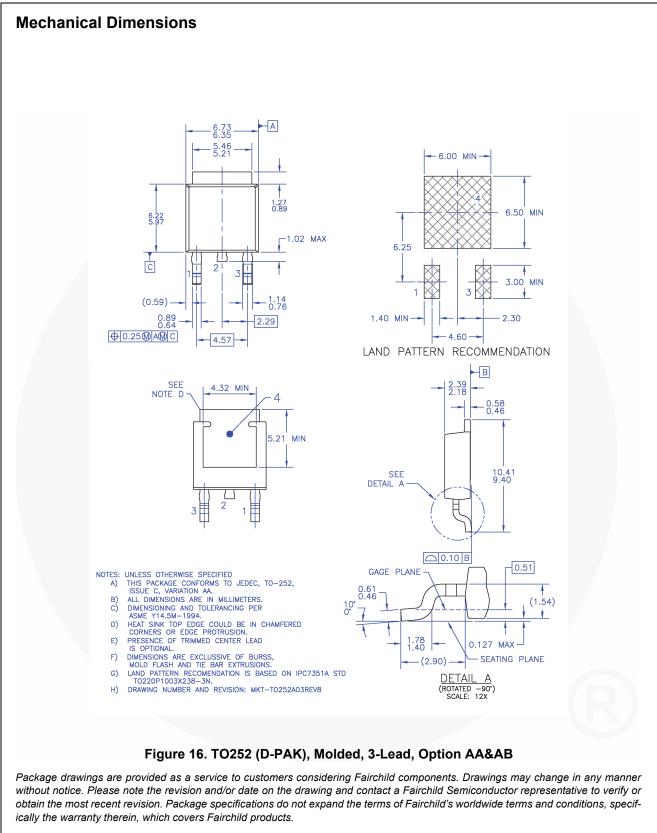
Part Number FQD7N20LTM		Top Mark	Pack	age	Packing Method Re		Size	Tape Width		Quantity 2500 units	
		FQD7N20L	DP	DPAK Tape a		eel 330 mm		16 mi	m 2		
ectri	cal Cha	racteristics	T <sub>C</sub> = 25°0	C unless ot	nerwise noted.						
Symbol		Parameter	-		Test Condition	s	Min.	Тур.	Max.	Unit	
Off Cha	aracterist	ics									
BV <sub>DSS</sub>	Drain-Sou	ain-Source Breakdown Voltage		V <sub>GS</sub> =	0 V, I <sub>D</sub> = 250 μA		200			V	
$\Delta BV_{DSS}$ / $\Delta T_J$	Breakdown Voltage Temperature Coefficient		$I_D = 250 \ \mu\text{A}$ , Referenced to $25^{\circ}\text{C}$				0.17		V/°C		
I <sub>DSS</sub>	Zero Gate Voltage Drain Current		V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V					1	μA		
			V <sub>DS</sub> = 160 V, T <sub>C</sub> = 125°C					10	μΑ		
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward		$V_{GS}$ = 20 V, $V_{DS}$ = 0 V					100	nA		
I <sub>GSSR</sub>	Gate-Bod	y Leakage Current,	Reverse	V <sub>GS</sub> =	-20 V, V <sub>DS</sub> = 0 V				-100	nA	
On Cha	aracterist	ics									
V <sub>GS(th)</sub>	Gate Thre	shold Voltage		-	V <sub>GS</sub> , I <sub>D</sub> = 250 μA		1.0		2.0	V	
R <sub>DS(on)</sub>	Static Drain-Source		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 2.75 \text{ A}$				0.59	0.75	Ω		
~	On-Resist		_		5 V, I <sub>D</sub> = 2.75 A 30 V, I <sub>D</sub> = 2.75 A			0.62	0.78	0	
9 <sub>FS</sub>	Forward	ransconductance	_	V <sub>DS</sub> =	$30 \text{ V}, \text{ I}_{\text{D}} = 2.75 \text{ A}$			5.6		S	
Dynam	ic Chara	cteristics									
C <sub>iss</sub>	Input Cap	acitance		V <sub>DS</sub> =	25 V, V <sub>GS</sub> = 0 V, MHz			390	500	pF	
C <sub>oss</sub>	Output Ca	apacitance		f = 1.0				55	70	pF	
C <sub>rss</sub>	Reverse 7	Fransfer Capacitance	e					8.5	11	pF	
Switch	ing Char	acteristics									
t <sub>d(on)</sub>		Delay Time	_	V -				12	35	ns	
t <sub>r</sub>	Turn-On F	Rise Time	_	$V_{DD} =$ $R_G = 2$	100 V, I <sub>D</sub> = 6.5 A,			125	260	ns	
t <sub>d(off)</sub>	Turn-Off	Delay Time	-	$r_G - 2$	10 12	(Note 4)		20	50	ns	
t <sub>f</sub>	Turn-Off F	all Time						65	140	ns	
Q <sub>g</sub>	Total Gate	e Charge		Vpe =	160 V, I <sub>D</sub> = 6.5 A,			6.8	9.0	nC	
Q <sub>gs</sub>	Gate-Sou	rce Charge		V <sub>GS</sub> =	-	(Note 4)		1.6		nC	
Q <sub>gd</sub>	Gate-Drai	n Charge						3.4		nC	
									1		
Drain-S		ode Characteri				S			5.5	A	
I <sub>SM</sub>		Pulsed Drain-Source							22	A	
V <sub>SD</sub>		Irce Diode Forward							1.5	V	
t <sub>rr</sub>		Recovery Time	, onage	$V_{GS} = 0 V, I_S = 5.5 A$ $V_{GS} = 0 V, I_S = 6.5 A,$			110		ns		
		Recovery Charge			$t = 100 \text{ A}/\mu \text{s}$			0.44		μC	
Q <sub>rr</sub>								0.11		μΟ	











Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN\_TT252-003

FQD7N20L — N-Channel QFET<sup>®</sup> MOSFET



No Identification Needed

Obsolete

**Full Production** 

Not In Production

Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.

Datasheet contains specifications on a product that is discontinued by Fairchild

Semiconductor. The datasheet is for reference information only.

Rev. 166

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor has against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death ass

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC

### **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below :

614233C 648584F IRFD120 JANTX2N5237 FCA20N60\_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L SBVS138LT1G 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C BUK954R8-60E NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384 NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UFO-7B DMN1006UCA6-7